

Yidong Xia

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/7694416/publications.pdf>

Version: 2024-02-01

37
papers

691
citations

516710

16
h-index

580821

25
g-index

38
all docs

38
docs citations

38
times ranked

1218
citing authors

#	ARTICLE	IF	CITATIONS
1	ZnO nanowire optoelectronic synapse for neuromorphic computing. <i>Nanotechnology</i> , 2022, 33, 065205.	2.6	26
2	High-Performance Pentacene-Based Field-Effect Transistor Memory Using the Electrets of Polymer Blends. <i>Advanced Electronic Materials</i> , 2022, 8, .	5.1	10
3	High Visible-Light-Stimulated Plasticity in Optoelectronic Synaptic Transistors for Irradiation History-Dependent Learning. <i>Advanced Electronic Materials</i> , 2020, 6, 1901255.	5.1	13
4	MoS ₂ -based Charge-trapping synaptic device with electrical and optical modulated conductance. <i>Nanophotonics</i> , 2020, 9, 2475-2486.	6.0	36
5	Raman shift, Néel temperature, and optical band gap of NiO nanoparticles. <i>Physical Chemistry Chemical Physics</i> , 2020, 22, 5735-5739.	2.8	7
6	High-Performance Visible-Light Photodetectors built on 2D-Nanoplate-Assembled Large-Scale Bil ₃ Films. <i>Advanced Electronic Materials</i> , 2019, 5, 1900159.	5.1	20
7	High-intensity compact ultrasound assisted synthesis of porous N-doped graphene thin microsheets with well-dispersed near-spherical Ni ₂ P nanoflowers for energy storage. <i>Chemical Engineering Journal</i> , 2019, 361, 387-397.	12.7	21
8	Large electromechanical strain and electrostrictive effect in (1-x)(Bi _{0.5} Na _{0.5} TiO ₃ -SrTiO ₃)-xLiNbO ₃ ternary lead-free piezoelectric ceramics. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 200-211.	2.2	5
9	Light-controlled stateful logic operations using optoelectronic switches based on p-Si/HfO ₂ heterostructures. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	14
10	Synthesis of Easily Transferred 2D Layered Bil ₃ Nanoplates for Flexible Visible-Light Photodetectors. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 21527-21533.	8.0	50
11	Silicon-Based Hybrid Optoelectronic Devices with Synaptic Plasticity and Stateful Photoresponse. <i>Advanced Electronic Materials</i> , 2018, 4, 1800242.	5.1	21
12	Enhancement of resistive switching ratio induced by competing interfacial oxygen diffusion in tantalum oxide based memories with metal nitride electrode. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	8
13	Large-sized Pbl ₂ single crystal grown by co-solvent method for visible-light photo-detector application. <i>Materials Letters</i> , 2017, 193, 101-104.	2.6	30
14	Giant electromechanical strain response in lead-free SrTiO ₃ -doped (Bi _{0.5} Na _{0.5} TiO ₃ -BaTiO ₃)-LiNbO ₃ piezoelectric ceramics. <i>Journal of the American Ceramic Society</i> , 2017, 100, 4670-4679.	3.8	46
15	Piezoelectricity in two-dimensional covalent organic frameworks. <i>Journal of Applied Physics</i> , 2017, 121, 225112.	2.5	0
16	Al ₂ O ₃ -Cu ₂ O composite charge-trapping nonvolatile memory. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 928-933.	2.2	3
17	Encoding, training and retrieval in ferroelectric tunnel junctions. <i>Scientific Reports</i> , 2016, 6, 27022.	3.3	8
18	Strain tunable magnetism in SnX ₂ (X=S, Se) monolayers by hole doping. <i>Scientific Reports</i> , 2016, 6, 39218.	3.3	36

#	ARTICLE	IF	CITATIONS
19	Quantum spin Hall insulator phase in monolayer WTe ₂ by uniaxial strain. AIP Advances, 2016, 6, .	1.3	31
20	Synthesis of PbI ₂ nanowires for high sensitivity photodetectors. RSC Advances, 2016, 6, 59445-59449.	3.6	20
21	Heating power lowering by downscaling the cell dimensions in nanoscale filamentary resistive switching devices. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	1
22	Continuously-tuned tunneling behaviors of ferroelectric tunnel junctions based on BaTiO ₃ /La _{0.67} Sr _{0.33} MnO ₃ heterostructure. AIP Advances, 2014, 4, .	1.3	7
23	Memristive learning and memory functions in polyvinyl alcohol polymer memristors. AIP Advances, 2014, 4, .	1.3	20
24	Half-metallicity in graphitic C ₃ N ₄ nanoribbons: An ab initio study. Physica Status Solidi (B): Basic Research, 2014, 251, 1386-1392.	1.5	12
25	The roles of the dielectric constant and the relative level of conduction band of high-k composite with Si in improving the memory performance of charge-trapping memory devices. AIP Advances, 2014, 4, 117110.	1.3	4
26	The effect of thermal treatment induced inter-diffusion at the interfaces on the charge trapping performance of HfO ₂ /Al ₂ O ₃ nanolaminate-based memory devices. Journal of Applied Physics, 2013, 114, .	2.5	54
27	The chemically driven phase transformation in a memristive abacus capable of calculating decimal fractions. Scientific Reports, 2013, 3, 1230.	3.3	16
28	Enhanced memory performance by tailoring the microstructural evolution of (ZrO ₂) _{0.6} (SiO ₂) _{0.4} charge trapping layer in the nanocrystallites-based charge trap flash memory cells. Applied Physics A: Materials Science and Processing, 2012, 108, 217-222.	2.3	15
29	Binary semiconductor In ₂ Te ₃ for the application of phase-change memory device. Journal of Materials Science, 2010, 45, 3569-3574.	3.7	16
30	Ga ₂ Te ₃ phase change material for low-power phase change memory application. Applied Physics Letters, 2010, 97, .	3.3	39
31	UV EMISSION OF TETRAGONAL ZrO ₂ NANOCRYSTALS EMBEDDED IN ZrSiO ₄ AMORPHOUS MATRIX. Modern Physics Letters B, 2010, 24, 2477-2483.	1.9	2
32	Robust Dirac point in honeycomb-structure nanoribbons with zigzag edges. Physical Review B, 2010, 81, .	3.2	12
33	Electrical field induced precipitation reaction and percolation in Ag ₃₀ Ge ₁₇ Se ₅₃ amorphous electrolyte films. Applied Physics Letters, 2009, 94, 162112.	3.3	25
34	Studies of two distinct types of (Ba,Sr)TiO ₃ /Pt interfaces. Applied Physics Letters, 2008, 92, 102906.	3.3	11
35	An investigation into ultra-thin pseudobinary oxide (TiO ₂) _x (Al ₂ O ₃) _{1-x} films as high-k gate dielectrics. Applied Physics A: Materials Science and Processing, 2007, 90, 379-384.	2.3	17
36	Effects of applied electric field during postannealing on the tunable properties of (Ba,Sr)TiO ₃ thin films. Applied Physics Letters, 2005, 87, 052902.	3.3	9

#	ARTICLE	IF	CITATIONS
37	Electrical properties of chemical-solution-derived Bi _{3.54} Nd _{0.46} Ti ₃ O ₁₂ ferroelectric thin films. Journal of Applied Physics, 2003, 94, 7376-7378.	2.5	26